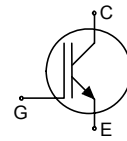


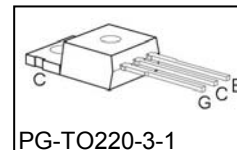
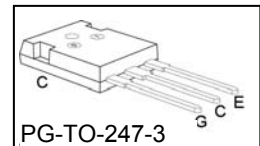
## HighSpeed 2-Technology

- Designed for:
  - SMPS
  - Lamp Ballast
  - ZVS-Converter
  - optimised for soft-switching / resonant topologies



- 2<sup>nd</sup> generation HighSpeed-Technology for 1200V applications offers:

- loss reduction in resonant circuits
- temperature stable behavior
- parallel switching capability
- tight parameter distribution
- $E_{off}$  optimized for  $I_C = 3A$



- Qualified according to JEDEC<sup>2</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>

Type	$V_{CE}$	$I_C$	$E_{off}$	$T_j$	Marking	Package
IGW03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-247-3
IGP03N120H2	1200V	3A	0.15mJ	150°C	G03H1202	PG-TO-220-3-1

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
Triangular collector current	$I_C$	9.6 3.9	A
$T_C = 25^\circ\text{C}, f = 140\text{kHz}$			
$T_C = 100^\circ\text{C}, f = 140\text{kHz}$			
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	9.9	
Turn off safe operating area	-	9.9	
$V_{CE} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$			
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Power dissipation	$P_{tot}$	62.5	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	$T_j, T_{stg}$	-40...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

<sup>2</sup> J-STD-020 and JESD-022

### Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		2.0	K/W
Thermal resistance, junction – ambient	$R_{thJA}$	PG-TO-220-3-1 PG-TO-247-3	62 40	

### Electrical Characteristic, at $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=300\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=3A$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$ $V_{GE} = 10V, I_C=3A,$ $T_j=25\text{ }^\circ\text{C}$	- - -	2.2 2.5 2.4	2.8 - -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=90\mu A, V_{CE}=V_{GE}$	2.1	3	3.9	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25\text{ }^\circ\text{C}$ $T_j=150\text{ }^\circ\text{C}$	- -	- -	20 80	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=3A$	-	2	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{ MHz}$	-	205	-	pF
Output capacitance	$C_{oss}$		-	24	-	
Reverse transfer capacitance	$C_{riss}$		-	7	-	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=3A$ $V_{GE}=15V$	-	22	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$	PG-TO-220-3-1 PG-TO-247-3	- -	7 13	- -	nH

**Switching Characteristic, Inductive Load, at  $T_j=25^\circ\text{C}$**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25^\circ\text{C}$ , $V_{CC}=800\text{V}$ , $I_C=3\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=82\Omega$ , $L_\sigma^{2)}=180\text{nH}$ , $C_\sigma^{2)}=40\text{pF}$ Energy losses include "tail" and diode <sup>3)</sup> reverse recovery.	-	9.2	-	ns
Rise time	$t_r$		-	5.2	-	
Turn-off delay time	$t_{d(off)}$		-	281	-	
Fall time	$t_f$		-	29	-	
Turn-on energy	$E_{on}$		-	0.14	-	mJ
Turn-off energy	$E_{off}$		-	0.15	-	
Total switching energy	$E_{ts}$		-	0.29	-	

**Switching Characteristic, Inductive Load, at  $T_j=150^\circ\text{C}$**

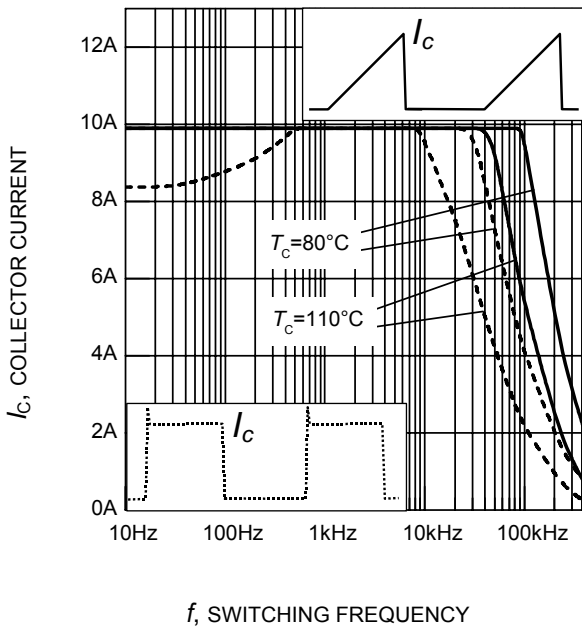
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150^\circ\text{C}$ $V_{CC}=800\text{V}$ , $I_C=3\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=82\Omega$ , $L_\sigma^{2)}=180\text{nH}$ , $C_\sigma^{2)}=40\text{pF}$ Energy losses include "tail" and diode <sup>3)</sup> reverse recovery.	-	9.4	-	ns
Rise time	$t_r$		-	6.7	-	
Turn-off delay time	$t_{d(off)}$		-	340	-	
Fall time	$t_f$		-	63	-	
Turn-on energy	$E_{on}$		-	0.22	-	mJ
Turn-off energy	$E_{off}$		-	0.26	-	
Total switching energy	$E_{ts}$		-	0.48	-	

**Switching Energy ZVT, Inductive Load**

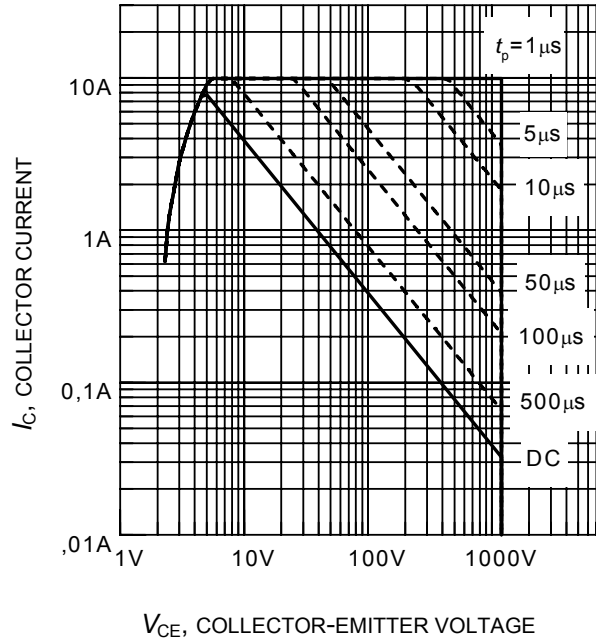
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-off energy	$E_{off}$	$V_{CC}=800\text{V}$ , $I_C=3\text{A}$ , $V_{GE}=15\text{V}/0\text{V}$ , $R_G=82\Omega$ , $C_r^{2)}=4\text{nF}$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.05	-	mJ
			-	0.09	-	

<sup>2)</sup> Leakage inductance  $L_\sigma$  and stray capacity  $C_\sigma$  due to dynamic test circuit in figure E

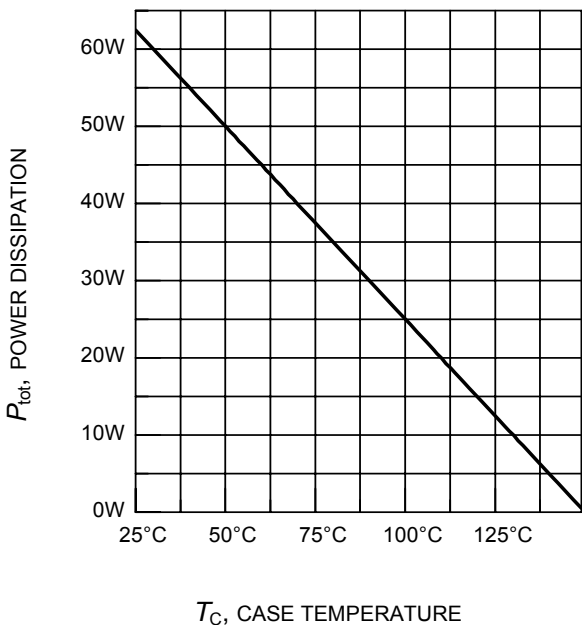
<sup>3)</sup> Commutation diode from device IKP03N120H2



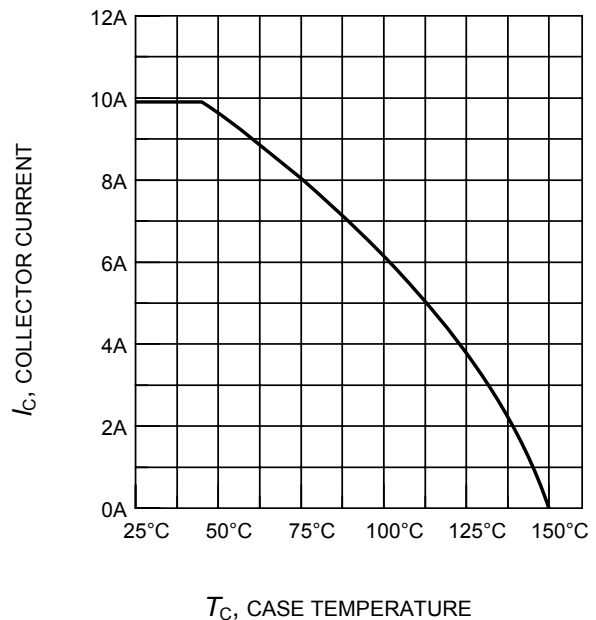
**Figure 1. Collector current as a function of switching frequency**  
( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ )



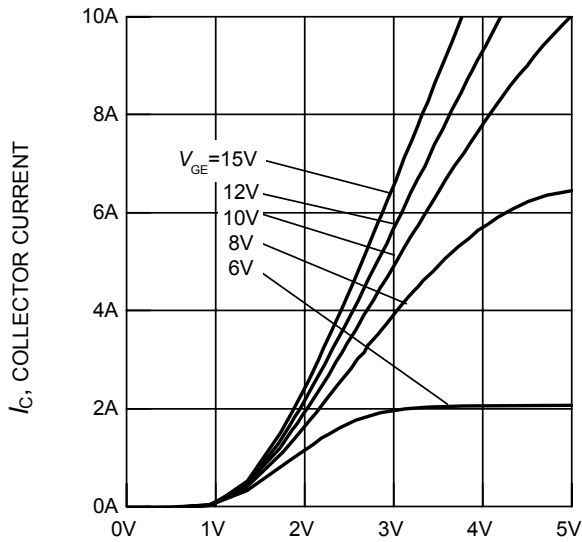
**Figure 2. Safe operating area**  
( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



**Figure 3. Power dissipation as a function of case temperature**  
( $T_j \leq 150^\circ\text{C}$ )

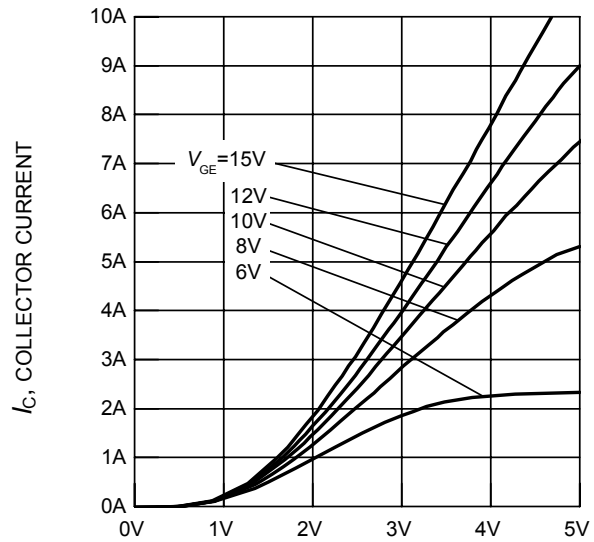


**Figure 4. Collector current as a function of case temperature**  
( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



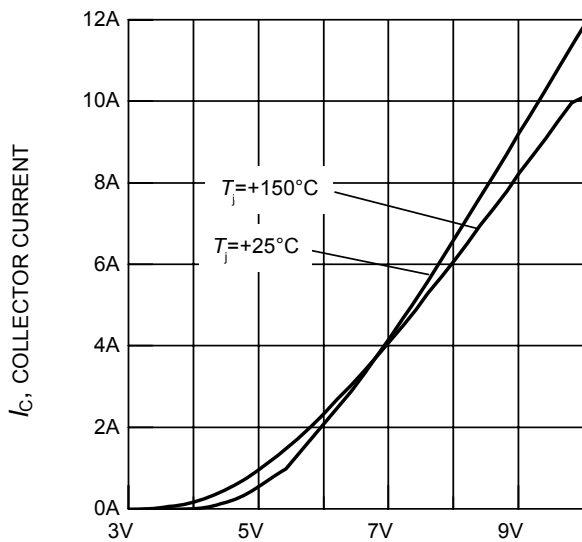
$V_{CE}$ , COLLECTOR-EMITTER VOLTAGE

**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



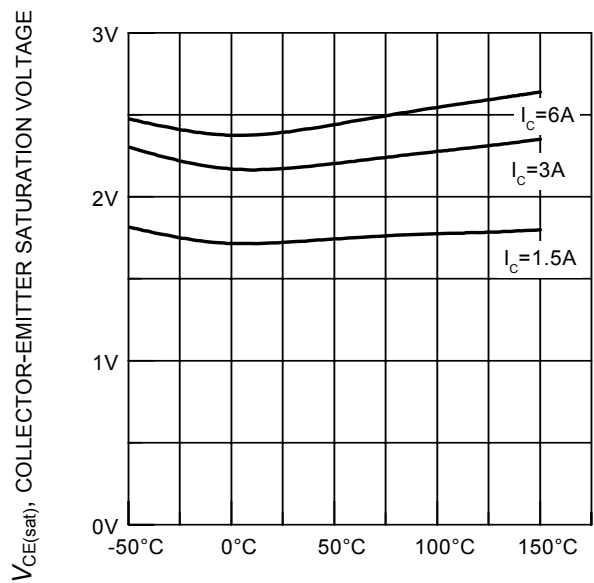
$V_{CE}$ , COLLECTOR-EMITTER VOLTAGE

**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



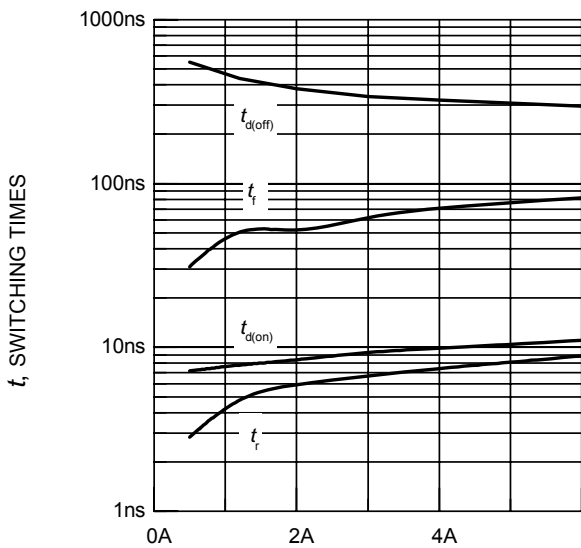
$V_{GE}$ , GATE-EMITTER VOLTAGE

**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 20\text{V}$ )



$T_j$ , JUNCTION TEMPERATURE

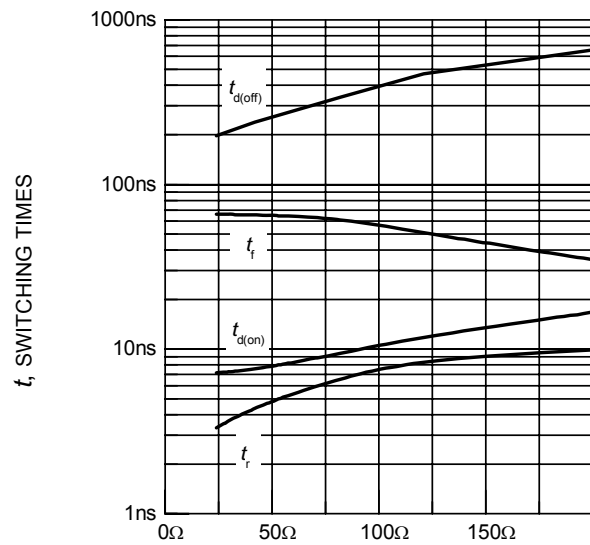
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



$I_C$ , COLLECTOR CURRENT

**Figure 9. Typical switching times as a function of collector current**

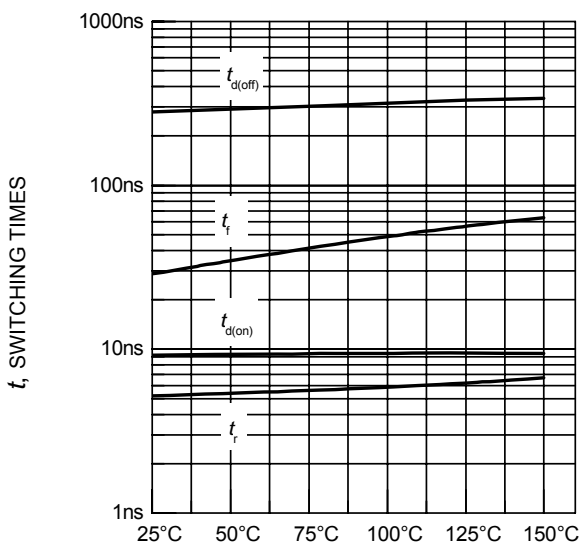
(inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ ,  
dynamic test circuit in Fig.E)



$R_G$ , GATE RESISTOR

**Figure 10. Typical switching times as a function of gate resistor**

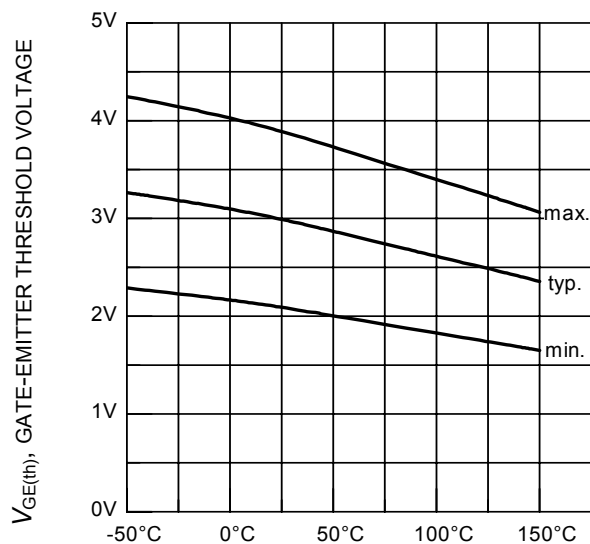
(inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ ,  
dynamic test circuit in Fig.E)



$T_j$ , JUNCTION TEMPERATURE

**Figure 11. Typical switching times as a function of junction temperature**

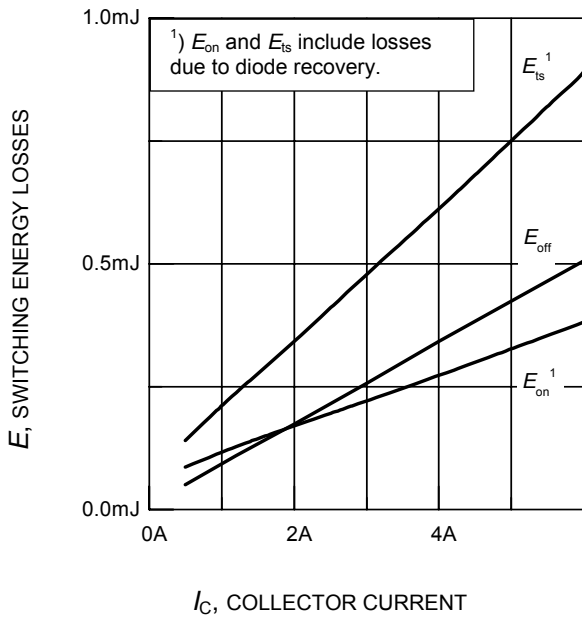
(inductive load,  $V_{CE} = 800\text{V}$ ,  
 $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ ,  $R_G = 82\Omega$ ,  
dynamic test circuit in Fig.E)



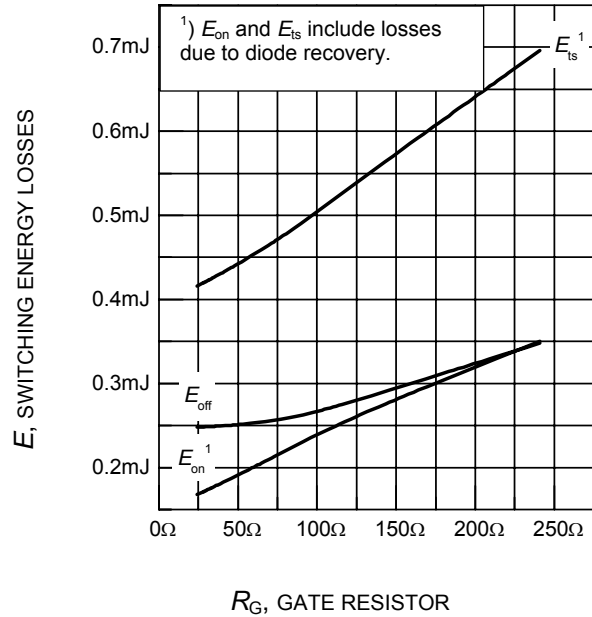
$T_j$ , JUNCTION TEMPERATURE

**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**

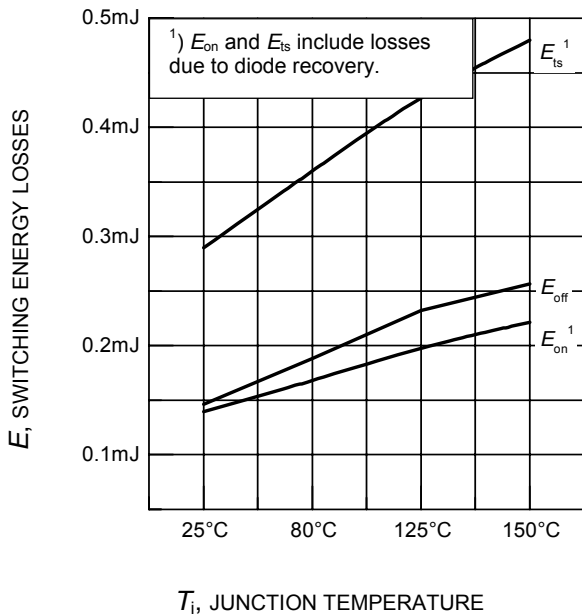
( $I_C = 0.09\text{mA}$ )



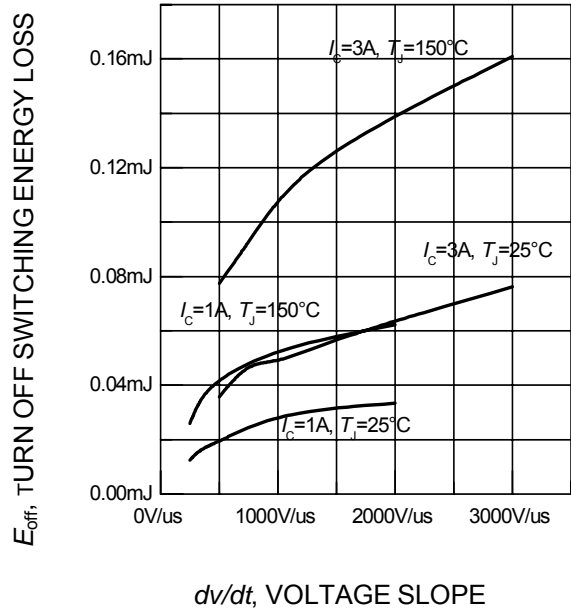
**Figure 13. Typical switching energy losses as a function of collector current**  
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E )



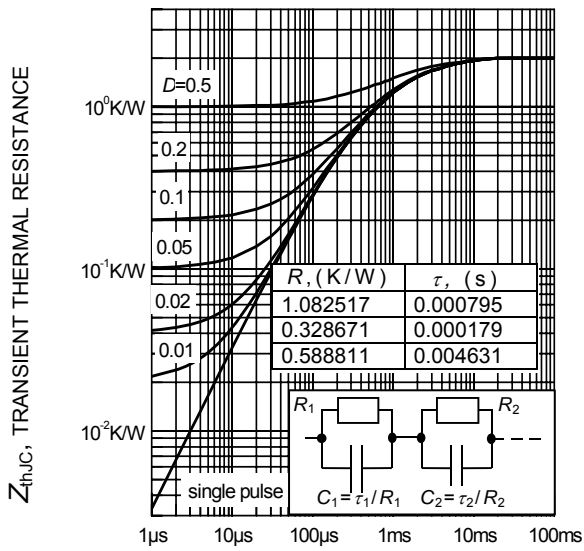
**Figure 14. Typical switching energy losses as a function of gate resistor**  
(inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ , dynamic test circuit in Fig.E )



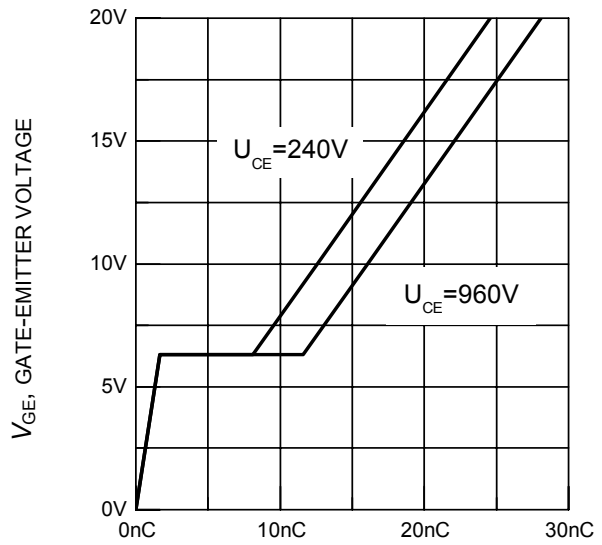
**Figure 15. Typical switching energy losses as a function of junction temperature**  
(inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 3\text{A}$ ,  $R_G = 82\Omega$ , dynamic test circuit in Fig.E )



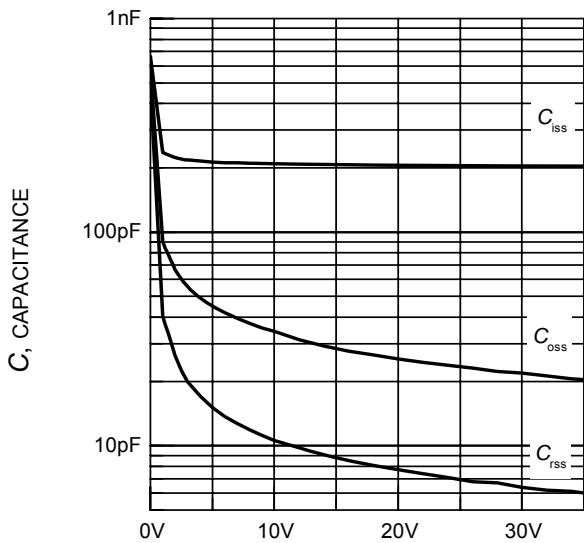
**Figure 16. Typical turn off switching energy loss for soft switching**  
(dynamic test circuit in Fig. E )



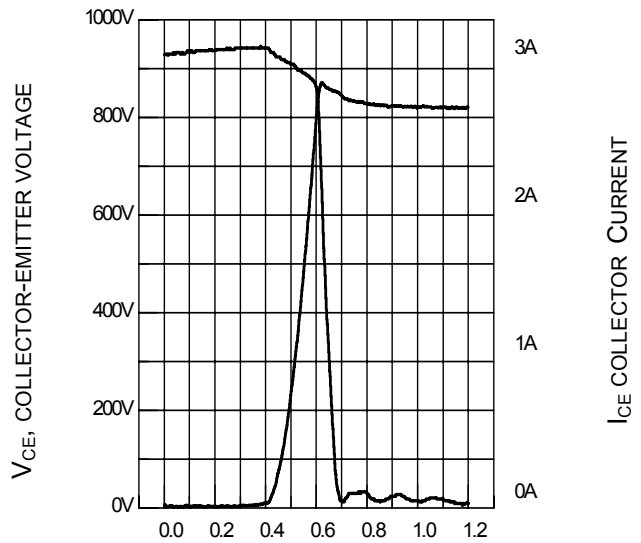
**Figure 16. IGBT transient thermal resistance**  
( $D = t_p / T$ )



**Figure 17. Typical gate charge**  
( $I_C = 3A$ )

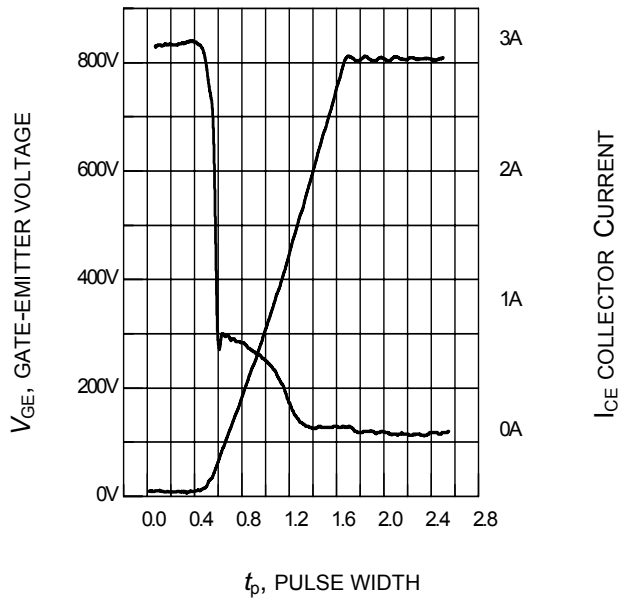


**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE} = 0V, f = 1MHz$ )



**Figure 20. Typical turn off behavior, hard switching**  
( $V_{GE} = 15/0V, R_G = 82\Omega, T_j = 150^\circ C$ ,  
Dynamic test circuit in Figure E)

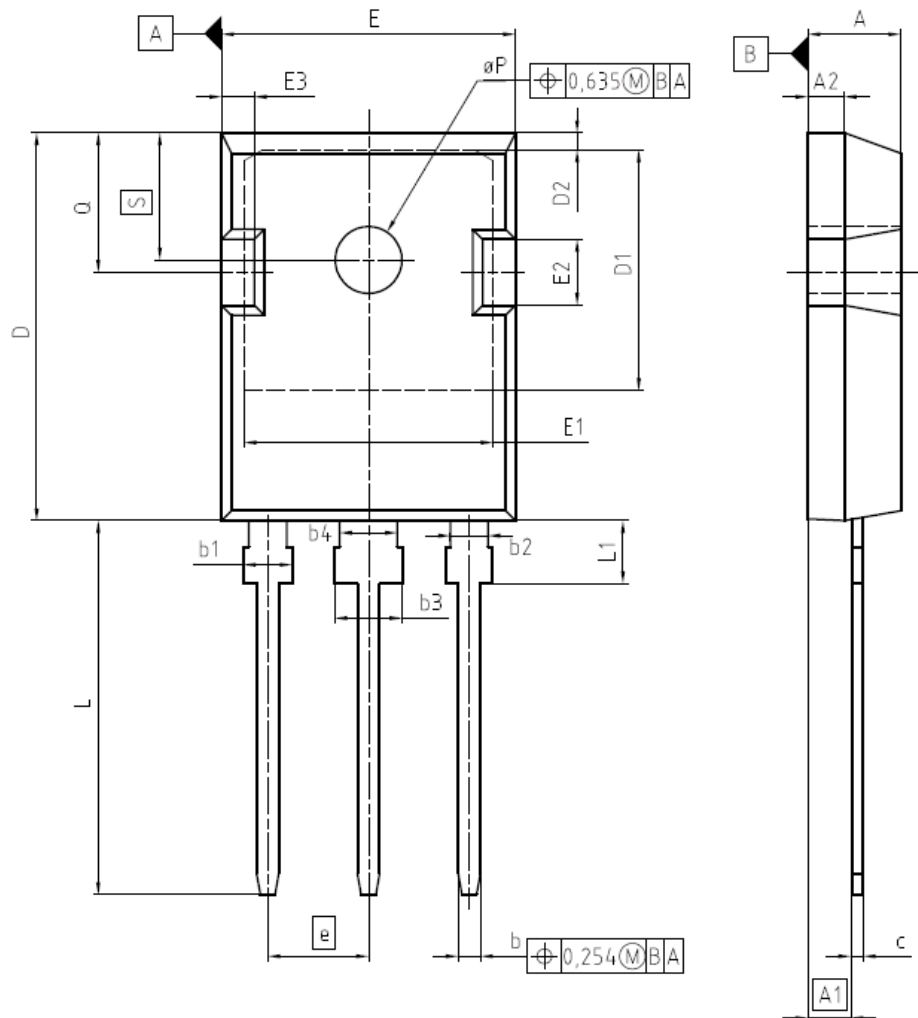




**Figure 21. Typical turn off behavior, soft switching**

( $V_{GE}=15/0V$ ,  $R_G=82\Omega$ ,  $T_j = 150^\circ C$ ,  
Dynamic test circuit in Figure E)

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,90	5,16	0,193	0,203
A1	2,27	2,53	0,089	0,099
A2	1,85	2,11	0,073	0,083
b	1,07	1,33	0,042	0,052
b1	1,90	2,41	0,075	0,095
b2	1,90	2,16	0,075	0,085
b3	2,87	3,38	0,113	0,133
b4	2,87	3,13	0,113	0,123
c	0,55	0,68	0,022	0,027
D	20,82	21,10	0,820	0,831
D1	16,25	17,65	0,640	0,695
D2	1,05	1,35	0,041	0,053
E	15,70	16,03	0,618	0,631
E1	13,10	14,15	0,516	0,557
E2	3,68	5,10	0,145	0,201
E3	1,68	2,60	0,066	0,102
e	5,44		0,214	
N	3		3	
L	19,80	20,31	0,780	0,799
L1	4,17	4,47	0,164	0,176
$\phi P$	3,50	3,70	0,138	0,146
Q	5,49	6,00	0,216	0,236
S	6,04	6,30	0,238	0,248

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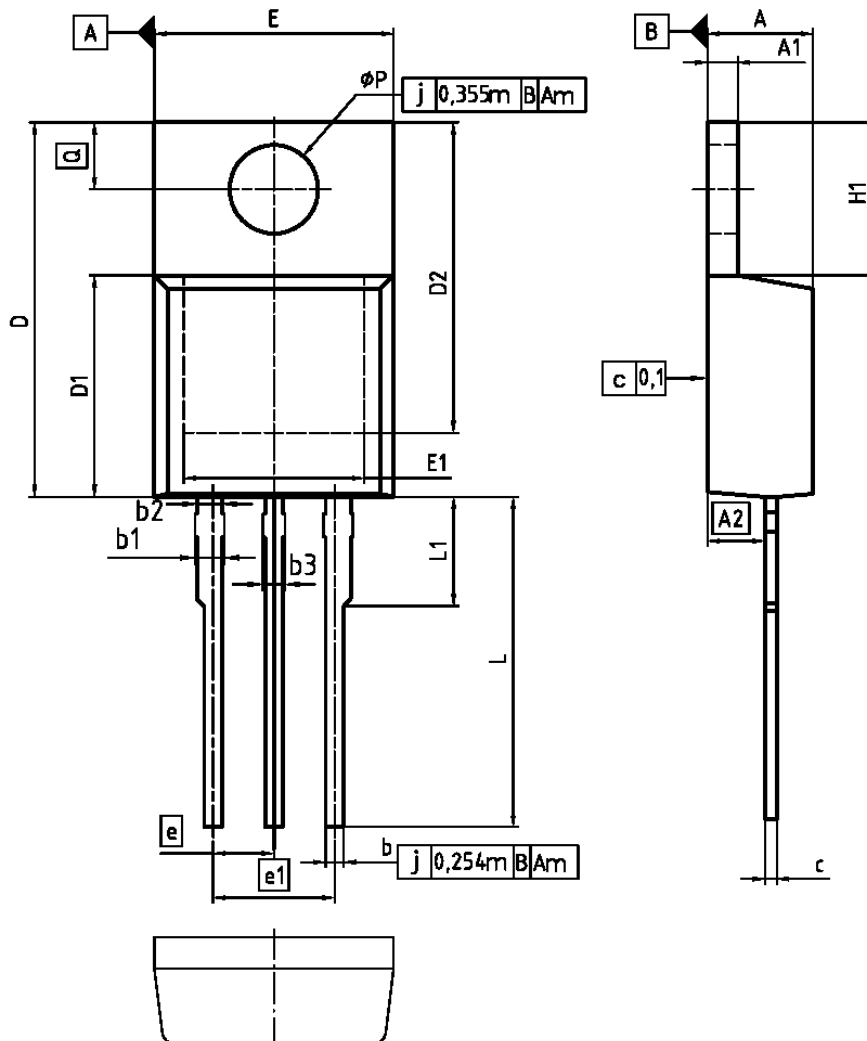
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ISSUE DATE  
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REVISION  
03

PG-TO220-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.85	1.15	0.028	0.045
c	0.33	0.80	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.518
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
phi P	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

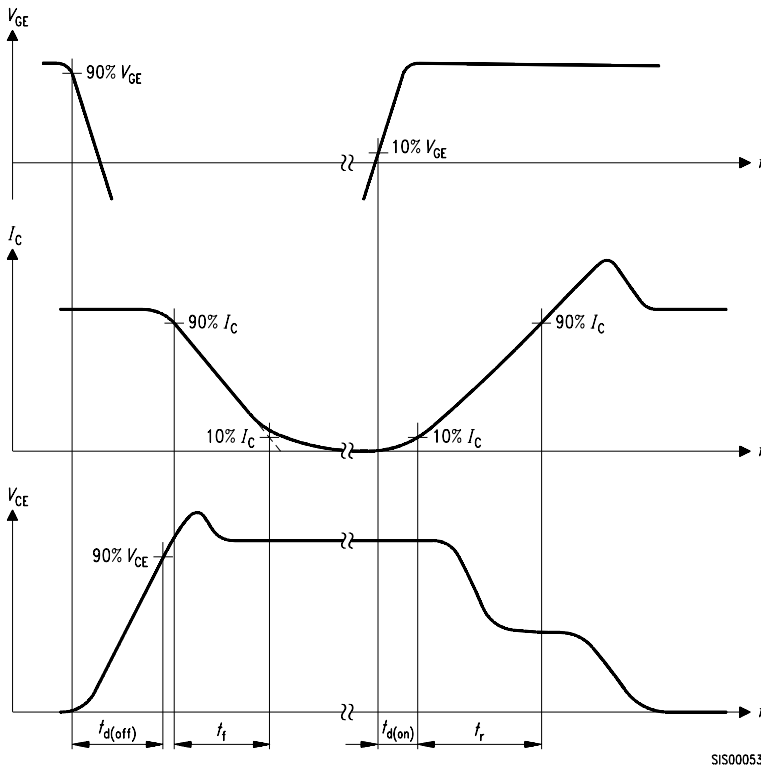
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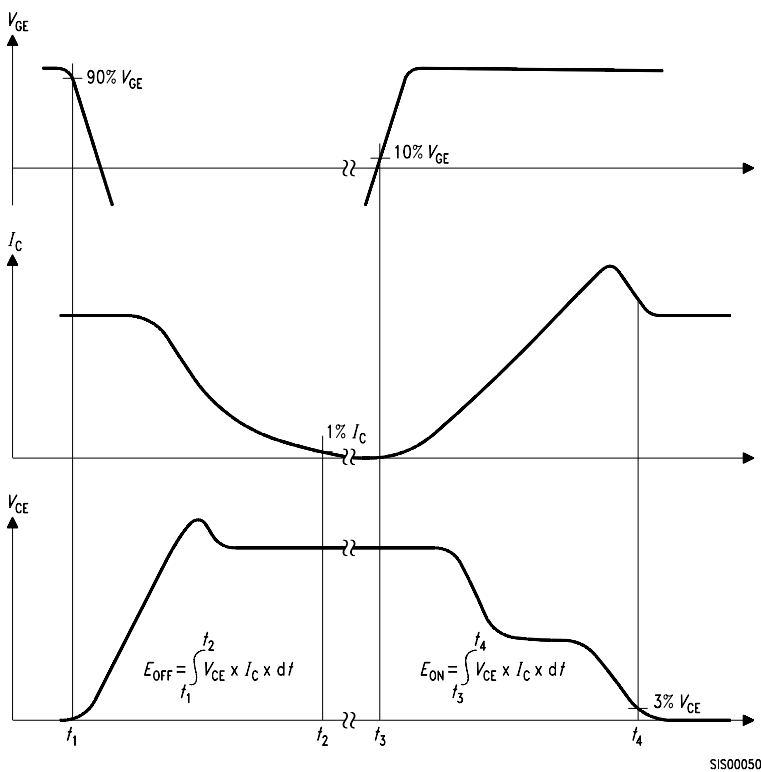
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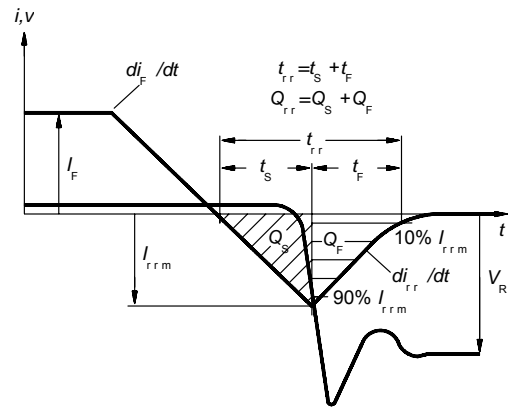
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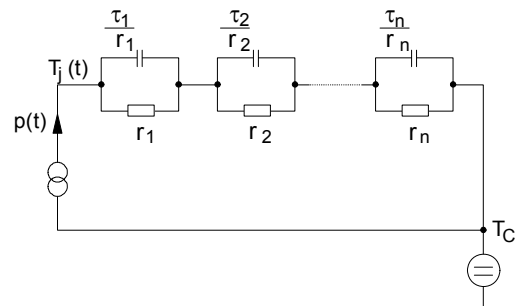
**Figure A. Definition of switching times**



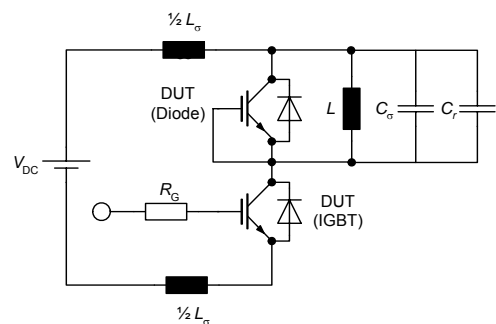
**Figure B. Definition of switching losses**



**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure E. Dynamic test circuit**  
Leakage inductance  $L_\sigma = 180\text{nH}$ ,  
Stray capacitor  $C_\sigma = 40\text{pF}$ ,  
Relief capacitor  $C_r = 4\text{nF}$  (only for ZVT switching)

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- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
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- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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